

FJPF9020

Monolithic Construction With Built In Base-Emitter Shunt Resistors

- High Collector-Base Breakdown Voltage : BV_{CBO} = -550V
- High DC Current Gain : $h_{FE} = 550$ @ $V_{CE} = -4V$, $I_{C} = -1A$ (Typ.)
- Industrial Use

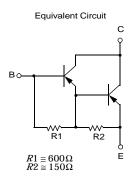


1.Base 2.Collector 3.Emitter

PNP Epitaxial Darlington Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	- 550	V
V _{CEO}	Collector-Emitter Voltage	- 550	V
V _{EBO}	Emitter-Base Voltage	- 6	V
I _C	Collector Current (DC)	- 2	Α
I _{CP}	Collector Current (Pulse)	- 4	Α
P _C	Collector Dissipation (T _C =25°C)	15	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C



Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = -100uA, I_E = 0$	- 550			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = -500uA, I_B = 0$	- 550			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = -200 \text{mA}, I_C = 0$	-6			V
I _{CBO}	Collector Cut-off Current	$V_{CE} = -550V, I_{E} = 0$			-100	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = -6V, I_{C} = 0$		-10	-20	mA
h _{FE}	DC Current Gain	V _{CE} = - 4V, I _C = - 1A	400	550	700	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = - 1A, I _B = - 20mA		-1.0	- 1.5	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = - 1A, I _B = - 20mA		-1.5	- 2.0	V

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Typical Characteristics

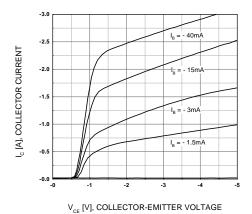


Figure 1. Static Characterstic

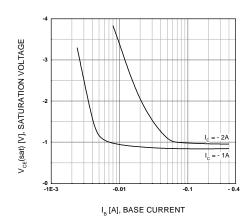


Figure 3. $V_{CE}(sat)$ vs. I_B Characteristics

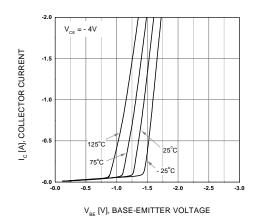


Figure 5. Base-Emitter On Voltage

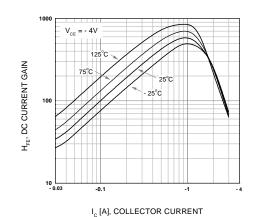


Figure 2. DC current Gain

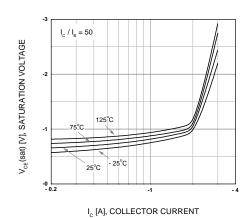


Figure 4. Collector-Emitter Saturation Voltage

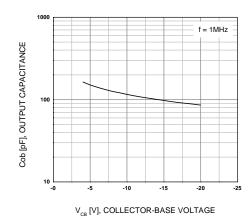


Figure 6. Output Capacitance

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Typical Characteristics (Continued)

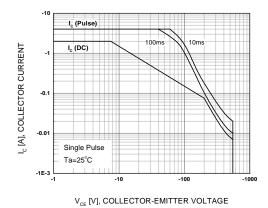


Figure 7. Forward Bias Safe Operating Area

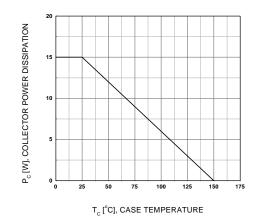
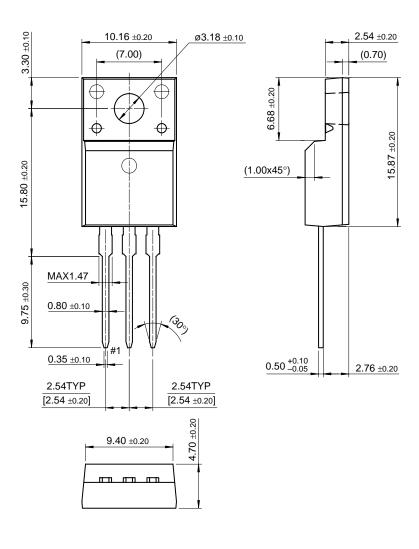


Figure 8. Power Derating

Package Demensions

TO-220F



Dimensions in Millimeters

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